

GSMDD0903

100V P-Channel MOSFETs

Product Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

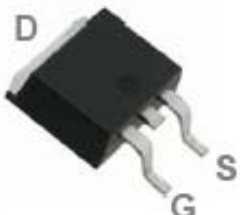
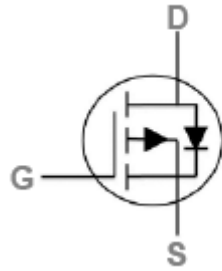
Features

- -100V, -10A, $R_{DS(ON)}=140m\Omega@V_{GS}=-10V$
- V_{GS} Guaranteed $\pm 25V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- TO-252-2L package design

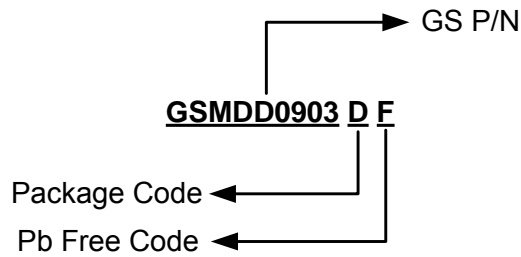
Applications

- Networking
- Load Switch
- LED applications

Packages & Pin Assignments

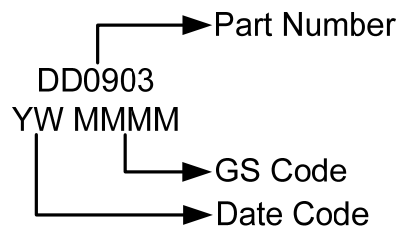
GSMDD0903DF (TO-252-2L)	
 <p>Top View</p>	
Description	
Gate	
Source	
Drain	

Ordering Information



Part Number	Package	Quantity Reel
GSMDD0903DF	TO-252-2L	2500 PCS

Marking Information



Absolute Maximum Ratings

T_C=25°C Unless otherwise noted

Symbol	Parameter	Typical	Unit
V _{DS}	Drain-Source Voltage	-100	V
V _{GS}	Gate –Source Voltage	±25	V
I _D	Continuous Drain Current	T _C =25°C	-10
		T _C =100°C	-6.5
I _{DM}	Pulsed Drain Current	-40	A
P _D	Power Dissipation (T _C =25°C)	88	W
	Power Dissipation (Derate above 25°C)	0.59	W/°C
T _J	Operating Junction Temperature Range	-55 to +150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient	62	°C/W
R _{θJC}	Thermal Resistance-Junction to Case	1.7	°C/W

Electrical Characteristics

T_J=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-100			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1		-3	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±25V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-100V, V _{GS} =0V			-1	μA
		V _{DS} =-80V, V _{GS} =0V, T _J =125°C			-10	
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			-10	A
I _{SM}	Pulsed Source Current				-20	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = -10V, I _D = -6A		115	140	mΩ
		V _{GS} = -4.5V, I _D = -3A		130	170	mΩ
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A			-1.2	V
Dynamic						
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-10V, I _D =-6A		40.4	70	nC
Q _{gs}	Gate-Source Charge			7.7	15	
Q _{gd}	Gate-Drain Charge			6.6	13	
C _{iss}	Input Capacitance	V _{DS} =-30V, V _{GS} =0V, f=1MHz		2250	3900	pF
C _{oss}	Output Capacitance			130	250	
C _{rss}	Reverse Transfer Capacitance			90	180	
t _{d(on)}	Turn-On Time	V _{DD} =-30V, I _D =-1A, V _{GS} =-10V, R _G =6Ω		27	54	ns
t _r				12	24	
t _{d(off)}	Turn-Off Time			150	300	
t _f				45	90	
R _g	Gate Resistance		V _{DS} =0V, V _{GS} =0V, f=1MHz		10	

Typical Performance Characteristics

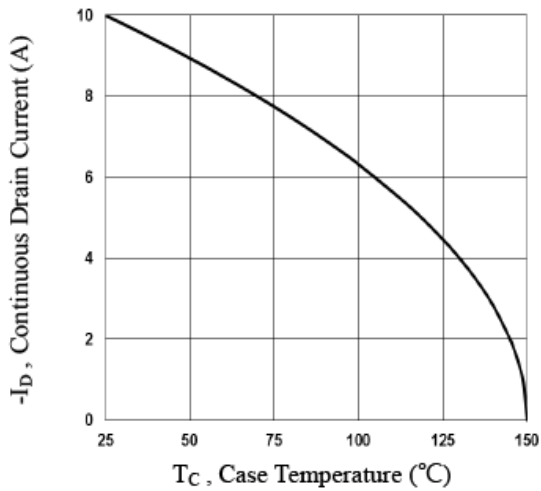


Fig.1 Continuous Drain Current vs. T_c

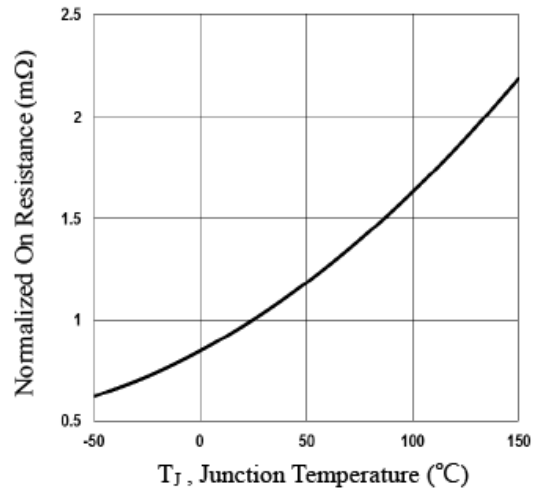


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

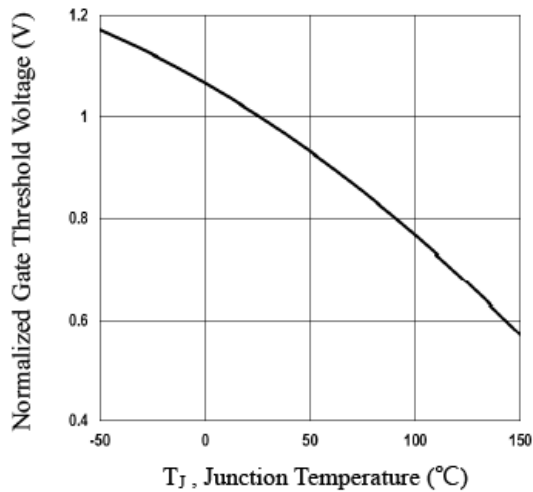


Fig.3 Normalized V_{th} vs. T_j

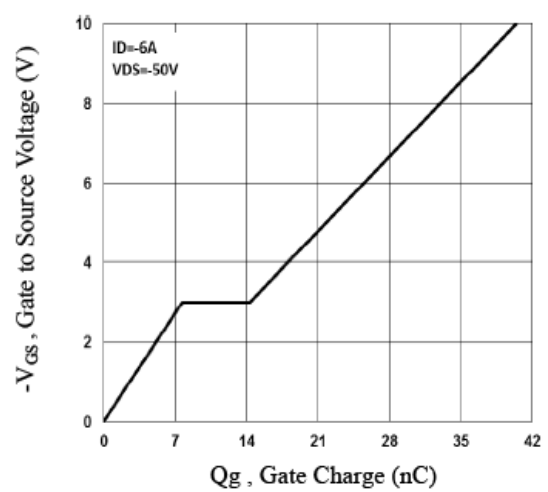


Fig.4 Gate Charge Waveform

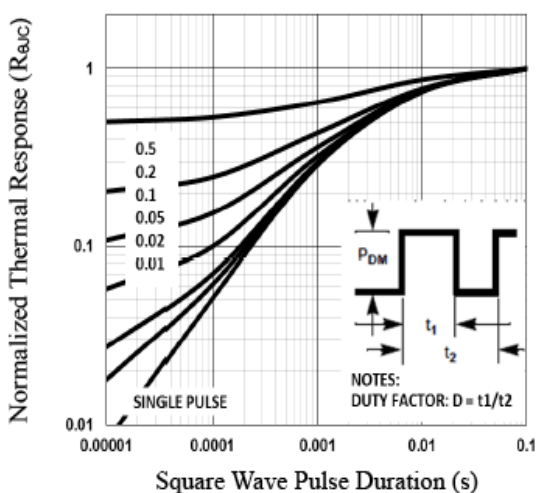


Fig.5 Normalized Transient Impedance

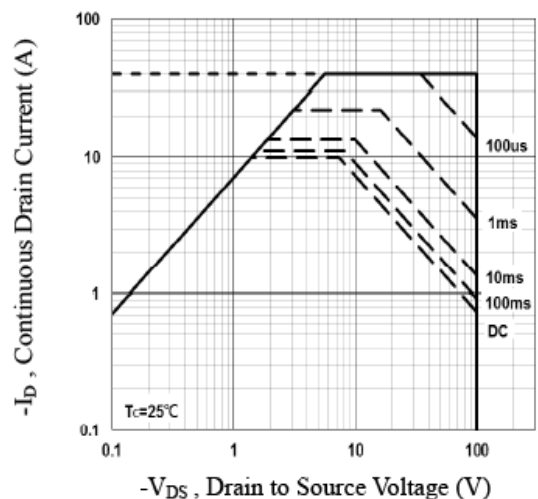
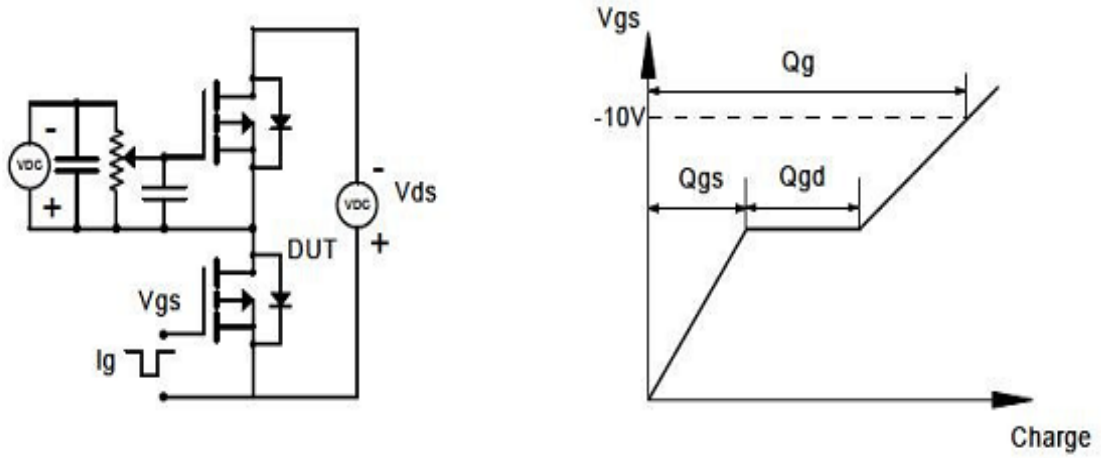


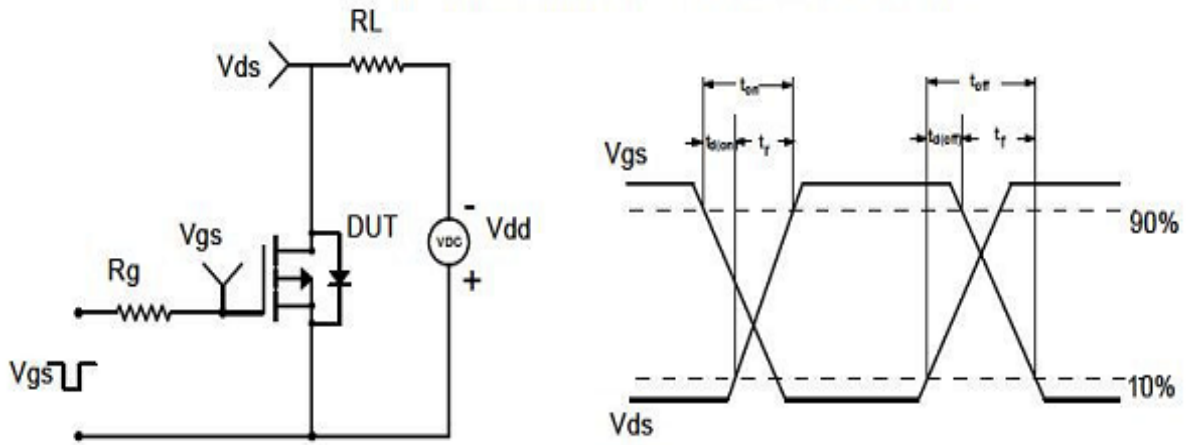
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

Gate Charge Test Circuit & Waveform

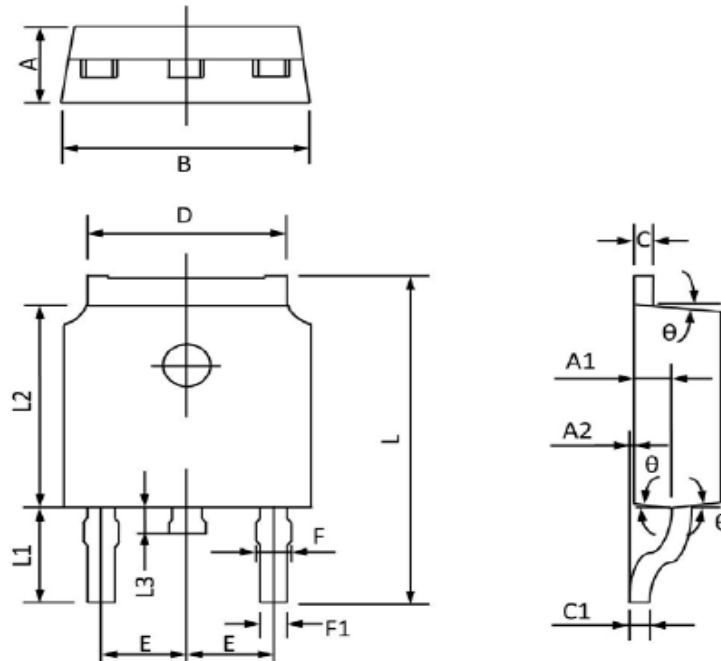


Resistive Switching Test Circuit & Waveforms



Package Dimension

TO-252-2L



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.20	2.40	0.087	0.094
A1	0.91	1.11	0.036	0.044
A2	0.00	0.15	0.000	0.006
B	6.40	6.80	0.252	0.268
C	0.46	0.58	0.018	0.030
C1	0.46	0.58	0.018	0.030
D	5.10	5.50	0.201	0.217
E	2.186	2.386	0.086	0.094
F	0.60	0.94	0.024	0.037
F1	0.50	0.86	0.020	0.034
L	9.40	10.40	0.370	0.409
L1	2.40	3.00	0.094	0.118
L2	5.40	6.20	0.213	0.244
L3	0.60	1.20	0.024	0.047
θ	3°	9°	3°	9°

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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Shenzhen Branch(China)	
	1113 B Building, Happiness Washington, Baoan Nan Road, Luohu District, Shenzhen City, China
	0755-22208941
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587